High-power distributed feedback semiconductor lasers operating at 2.05 μm range

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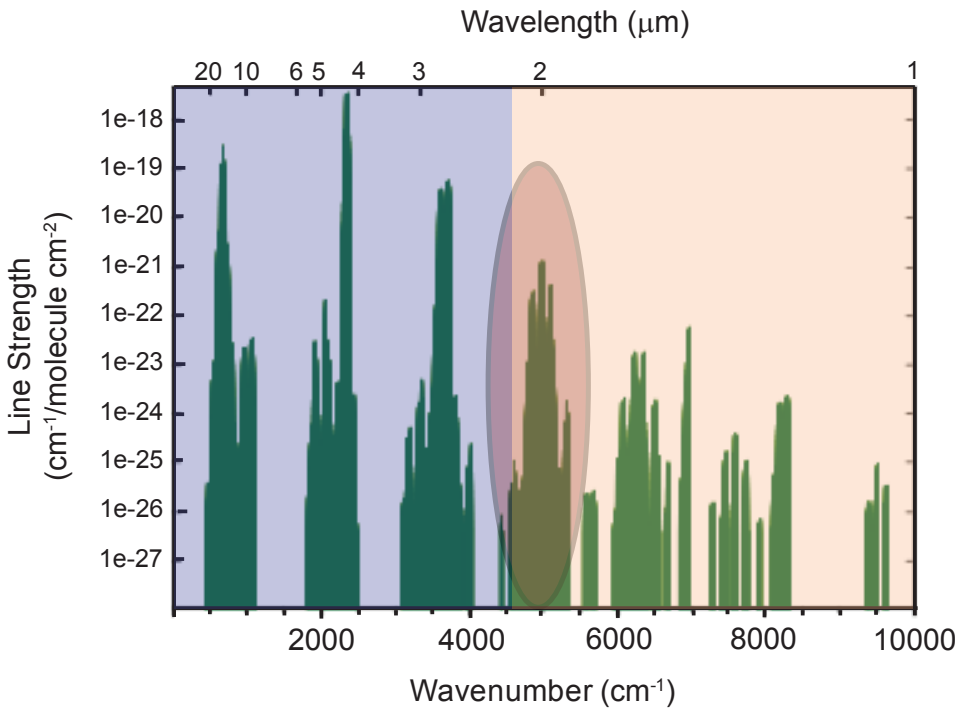
Motivation

- Integrated Path Differential Absorption (IPDA) lidar systems at both the 1.57 and 2.05 μm wavelength bands of CO_2 are being considered for space-born systems monitoring Earth atmosphere CO_2 dynamics
- The 2.05 μm band, with significantly stronger band strength, is more amenable to probing the atmosphere with weighting functions that emphasize the lowest few km above the surface
- The availability of off-the-shelf standard components, including semiconductor DFB lasers and optical amplifiers, has been a major driver in the adoption of 1.57 μm band for CO_2 lidars.
  - ✗ Current 2-μm lidar systems utilize rare-earth ion doped crystal lasers that are diode-pumped
- The recent development of high performance FPAs at mid-IR (1-4 μm) facilitates deployment of 2-μm lidar systems

A monolithic semiconductor seed laser operating at 2 μm wavelength bands of CO_2 would greatly enhance the operability and applicability of IPDA 2-μm lidar systems for airborne applications as well as the ASCENDS Earth-orbiting applications.

Active Remote CO_2 Monitoring

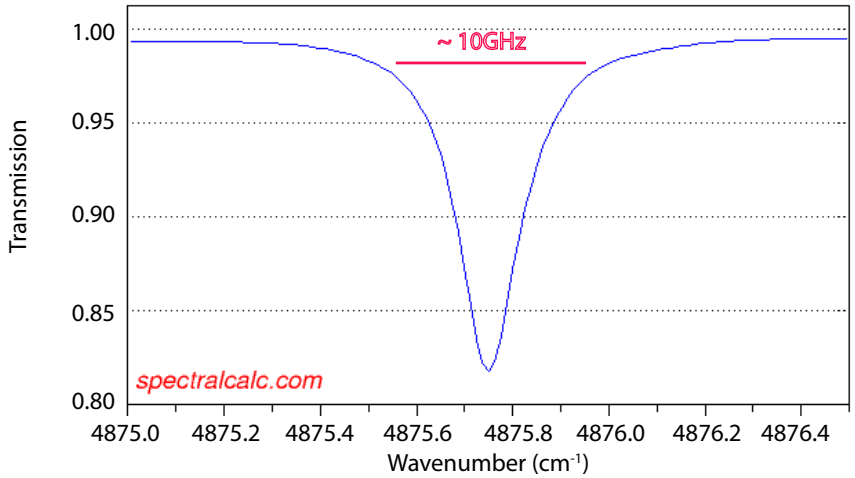
Figure: CO_2 molecular absorption spectrum



Lack of mature components (e.g. optical fiber amplifiers) beyond 2.1 μm

Smaller absorption strength < 2 μm

Figure: Pressure broadened CO_2 absorption line



The absorption spectrometer uses an on/off target gas absorption line to infer concentration

Lasers with reproducible tunability larger than absorption line width simplify system design

Semiconductor Lasers for Injection Seeding Applications

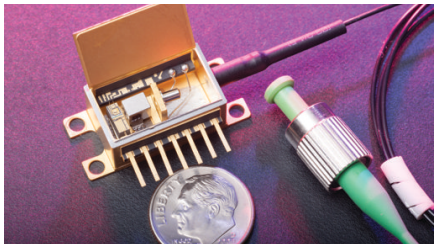
Solid-state lasers

- ✓ High output power
- ✓ Long coherence length (narrow linewidth)
- ✓ Circular beam ($M^2 \sim 1$)
- ✗ Limited tuning range <10 GHz
- ✗ Slow frequency modulation speeds <10 KHz
- ✗ Large thermal budget

Lockheed Martin Coherent Technologies METEOR laser

Semiconductor lasers

- ✓ Compact
- ✓ No moving parts (less susceptible to vibrations)
- ✓ Large tuning range >150 GHz
- ✓ Fast frequency and amplitude modulation speeds >1 GHz
- ✓ Low maintenance cost
- ✗ Larger linewidth



JPL's 2-μm butterfly package

Semiconductor laser's compact size, low thermal mass, and rugged architecture makes it highly suitable for airborne and space applications

Fiber-based Transmitters for Lidar Applications

All-fiber lidar architecture

- More compact and robust transmitter
- Easier to maintain (no optical alignment needed)
- Less susceptible to environmental vibrations
- Allows to use fiber amplifiers
- Using polarization maintaining optical fibers minimizes polarization drifts resulting in more sensitive measurements

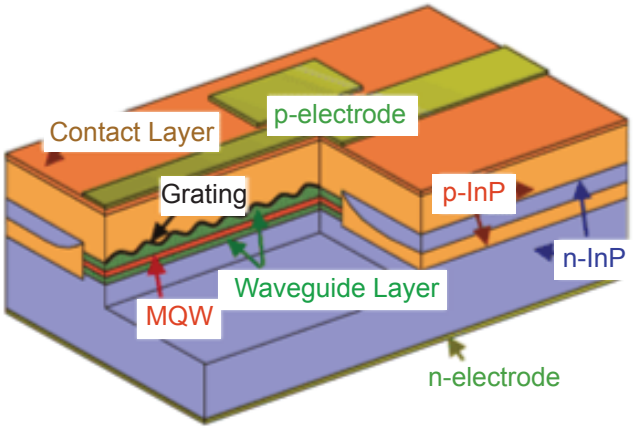
DFB Semiconductor Lasers for 2.05 μm Lidar Systems

Laser requirements

PM fiber output
$\sim$30 mW output power
$<$100 KHz laser linewidth

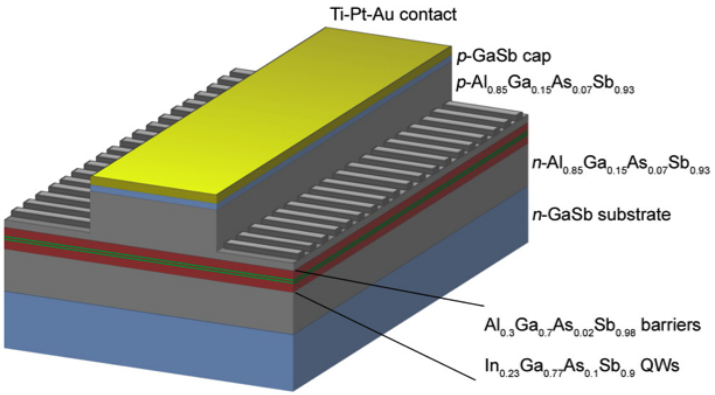
Strained InP lasers have limited output power
GaSb-based structures: no regrowth techniques
GaSb-based structures enable high power semiconductor lasers at mid-IR

Figure: Schematic representation of a conventional DFB structure using regrowth



T. Sato *et al. IEEE photon. Technol. Lett.* 20 (2008).

Figure: JPL's solution: laterally coupled DFB structure

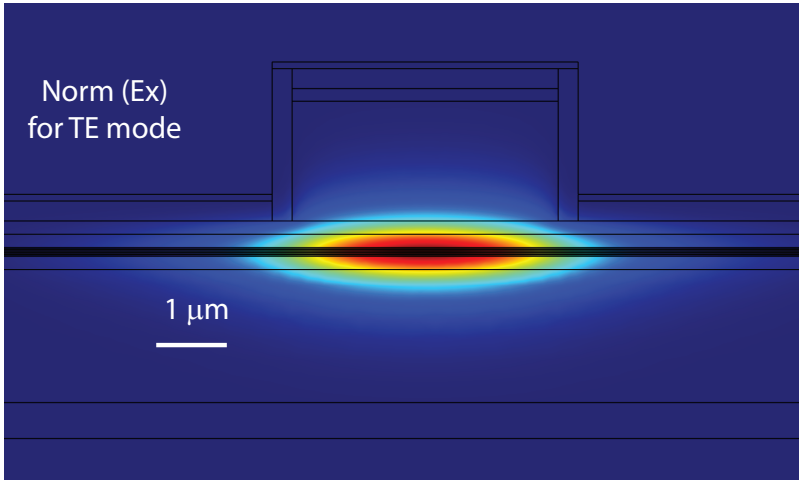


S. Forouhar *et al. Applied Physics Letters.* 100 (2012).

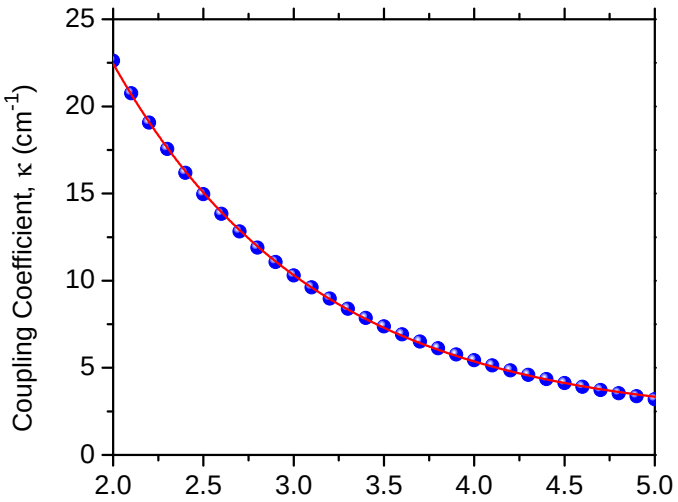
Laterally-coupled DFB InGaAsSb/AlGaAsSb multiple quantum well structures on GaSb was chosen as an alternative approach to achieve power requirements.

DFB Semiconductor Lasers for 2.05 μm Lidar Systems

Figure: Calculated optical mode

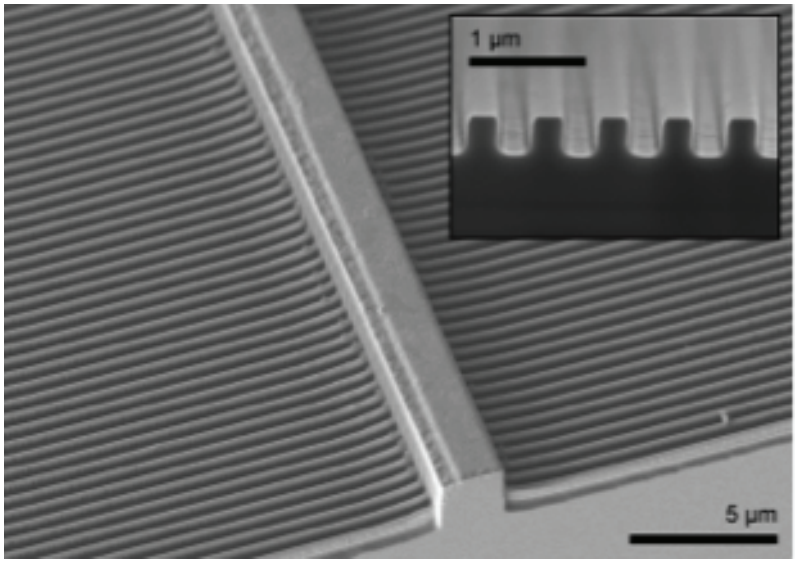


Calculated effective coupling strength



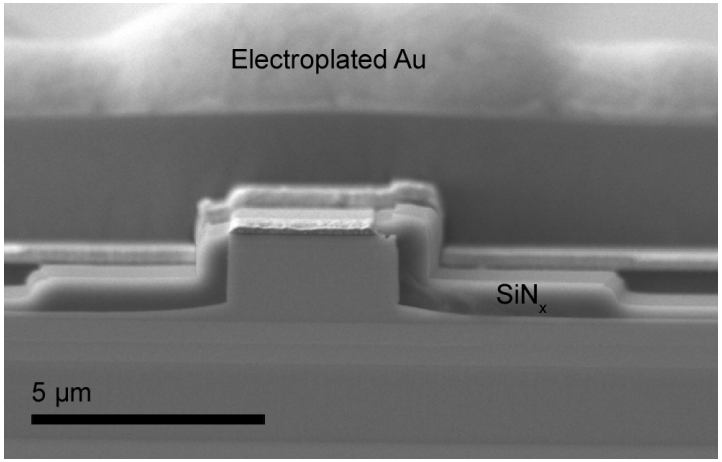
- Single-mode optical waveguides are etched into low-index cladding layer
- Second order gratings are etched along side ridges

  Helps suppress second DFB mode



Laterally Coupled GaSb-based Semiconductor DFB Lasers

Figure: LC-DFB laser after SiNx deposition and electroplating



- SiN_x isolation layer deposited by PECVD, followed by electroplating of thick Au top contacts
- Anti-reflection coating layer is applied to front facet
- Back facets are protected by passivation layers

Calculated/measured reflectivity spectra

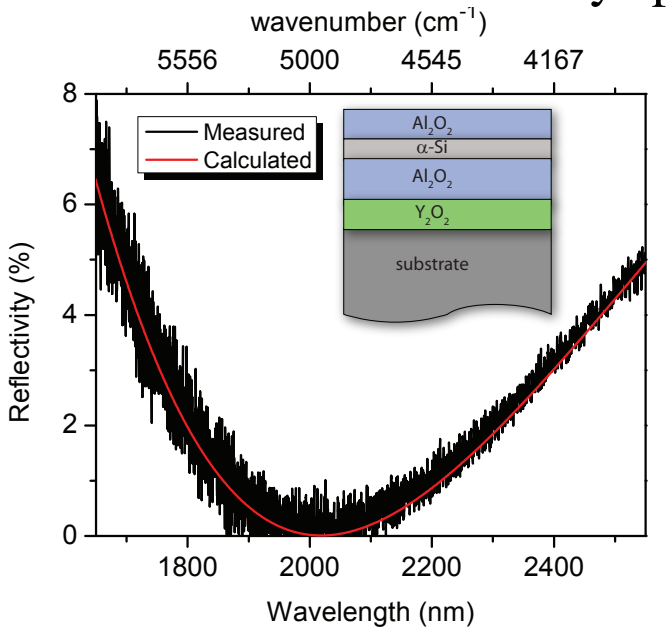
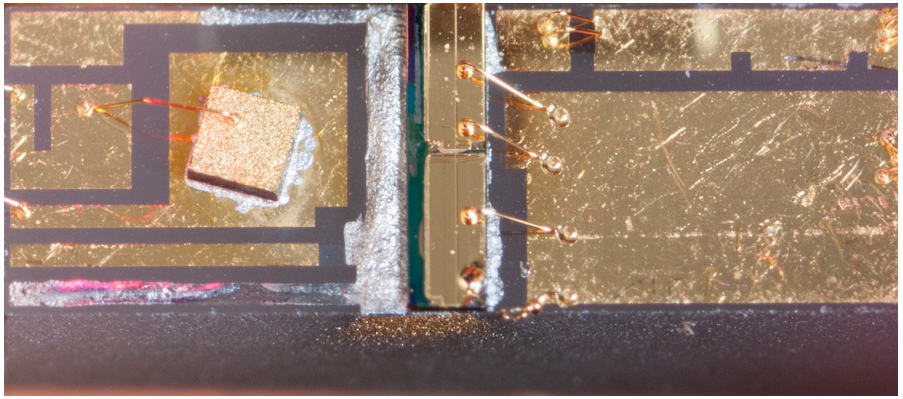
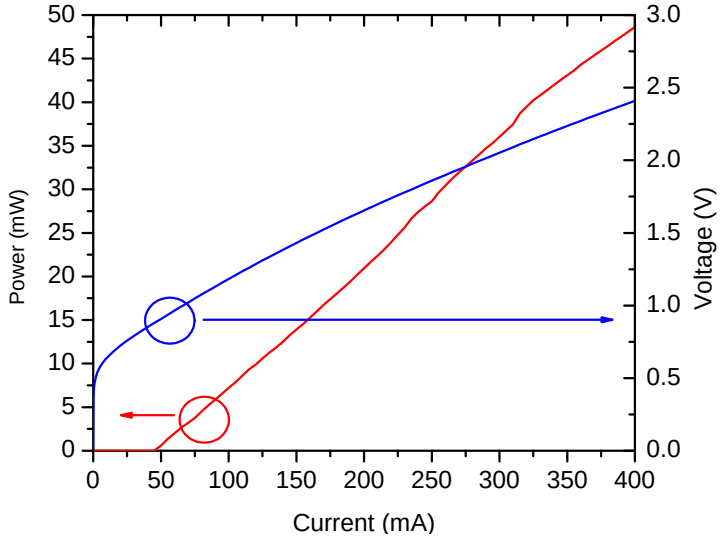


Figure: Mounted laser on submount

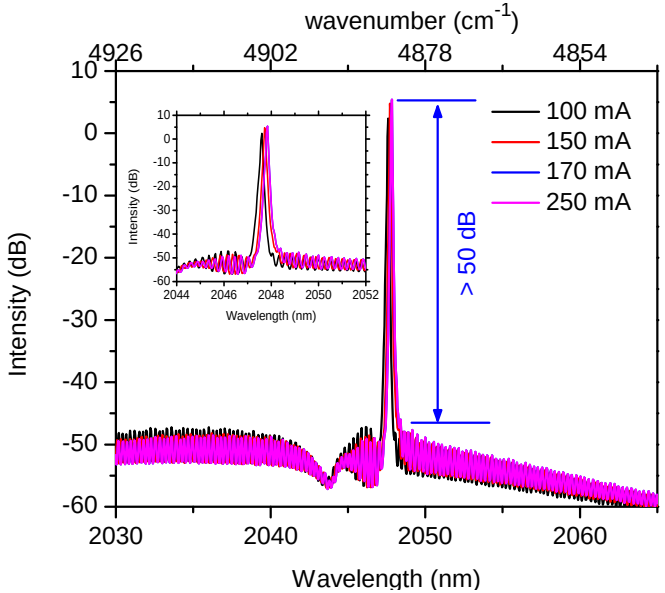


DFB Laser Performance

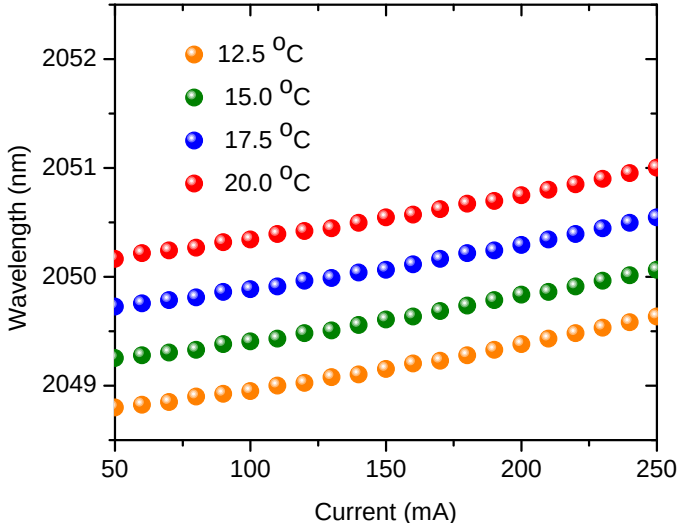
Output power versus input current

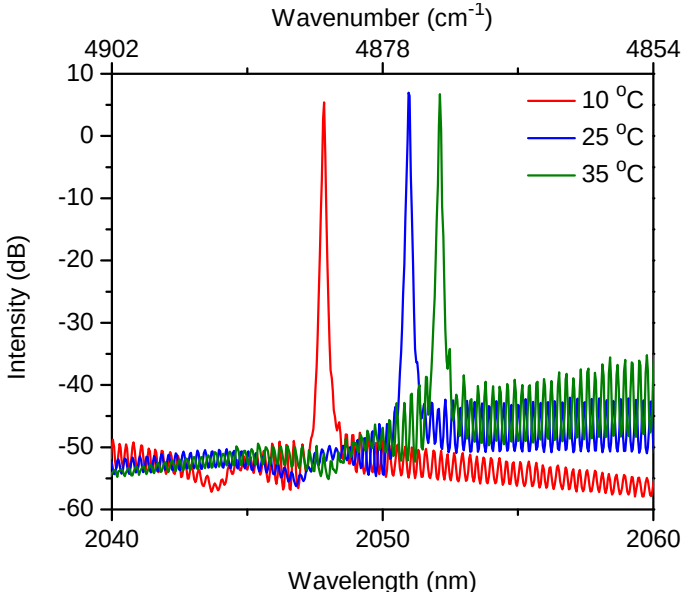


Lasing spectrum vs. bias current and temperature



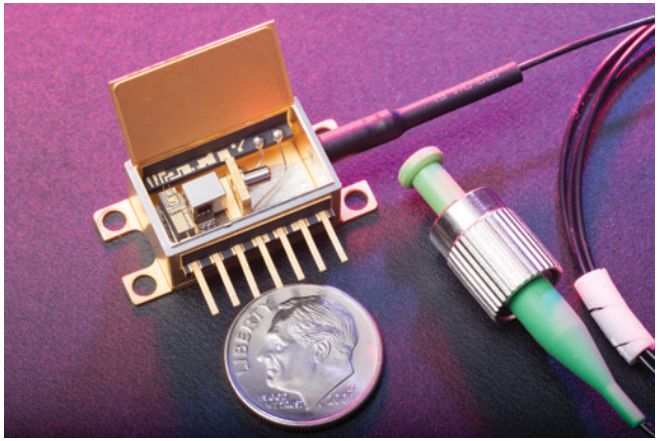
Wavelength tuning versus input current



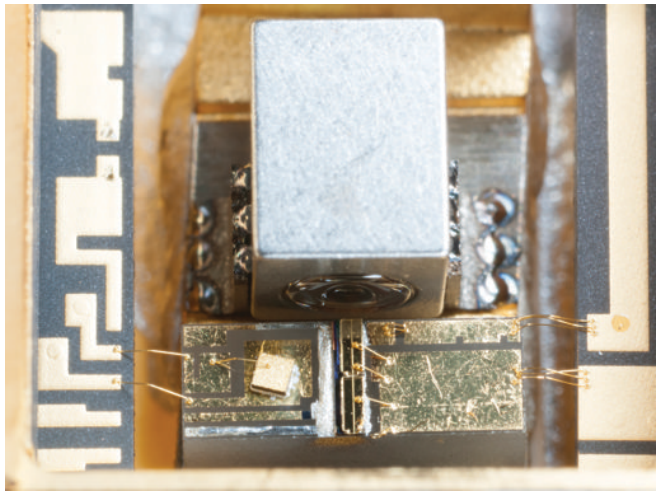


2.05 μm Laser Butterfly Packages

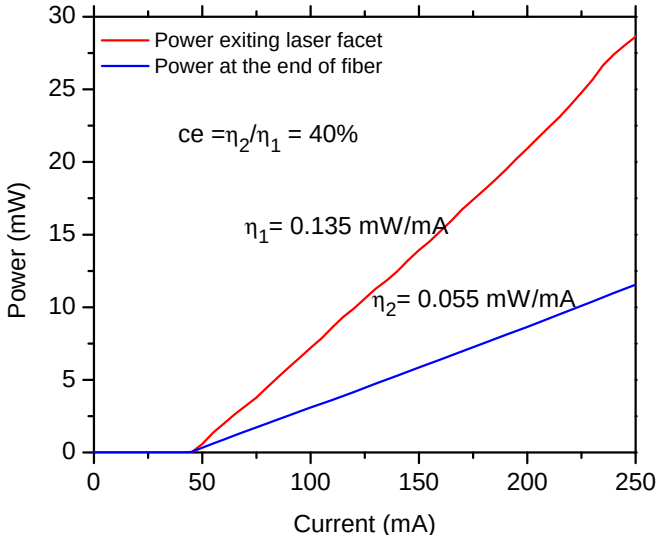
2.05 μm semiconductor laser butterfly package



2.05 μm butterfly components with integrated optical isolator



Measured coupling efficiency



40% coupling efficiency is demonstrated

>60% coupling efficiency can be achieved using double acylindrical lens with a focusing lens (3 lens scheme)

2.05 μm Linewidth Measurement Techniques

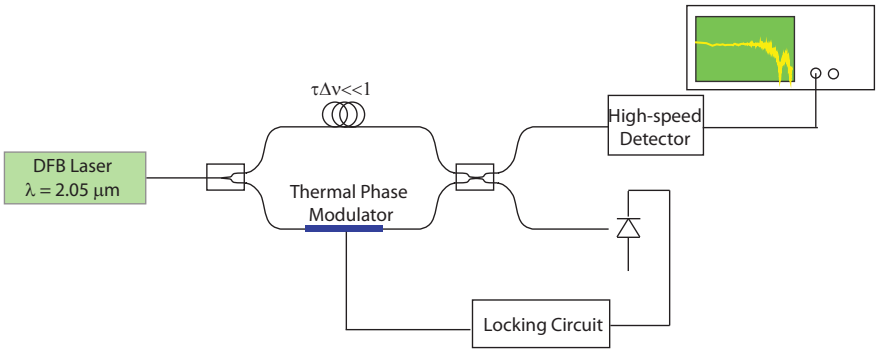
Heterodyne technique

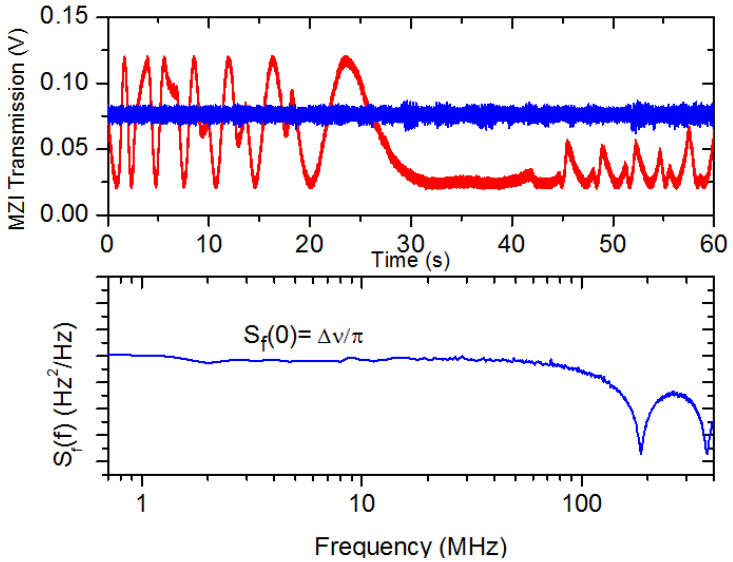
- ✓ Beat two similar laser with small frequency offset and look at the beating spectrum
- ✓ Relatively simple to implement
- ✗ Requires very stable lasers to minimize frequency drift

Self-delayed homodyne technique

- ✓ Beat one laser with its delayed replica
- ✓ Is insensitive to frequency jitter
- ✓ Simple to implement
- ✗ Requires long (>20 km) of single mode optical fiber

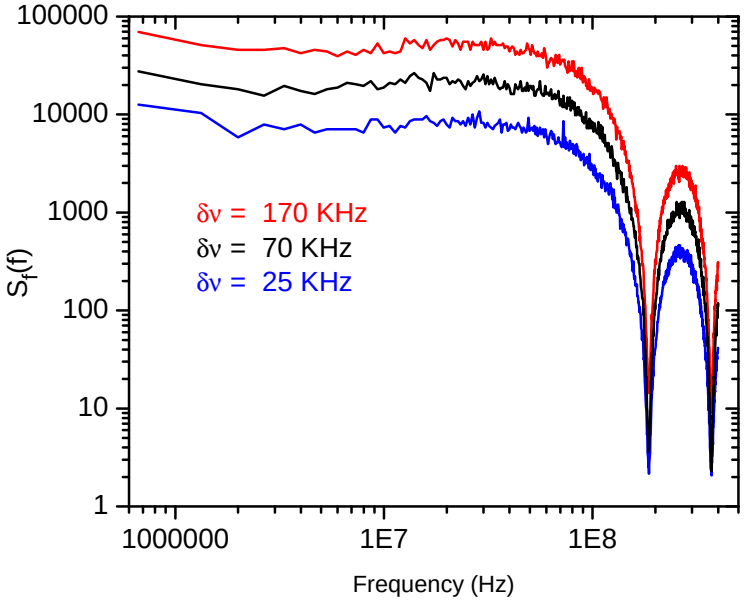
Frequency noise spectrum measurement setup



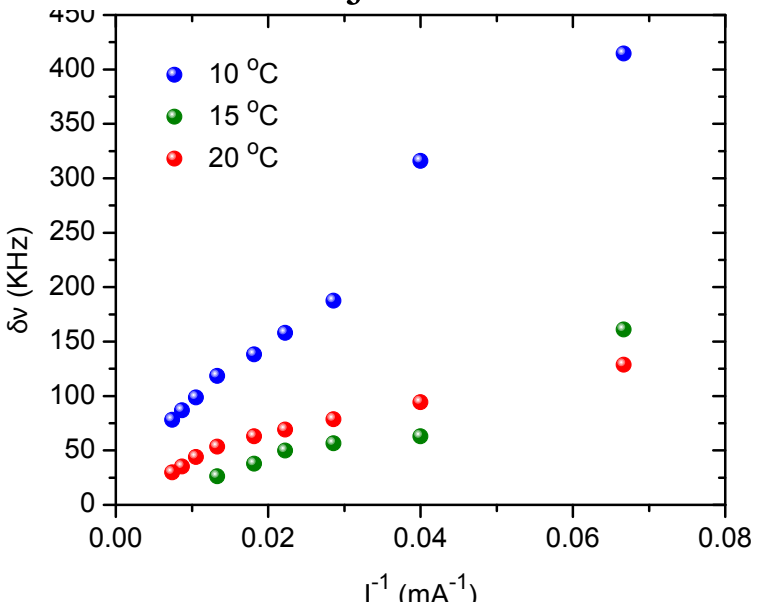


Laser Linewidth Measurement

Measured frequency noise spectrum at different bias current



Extracted Schallow-Townes linewidth versus injected current

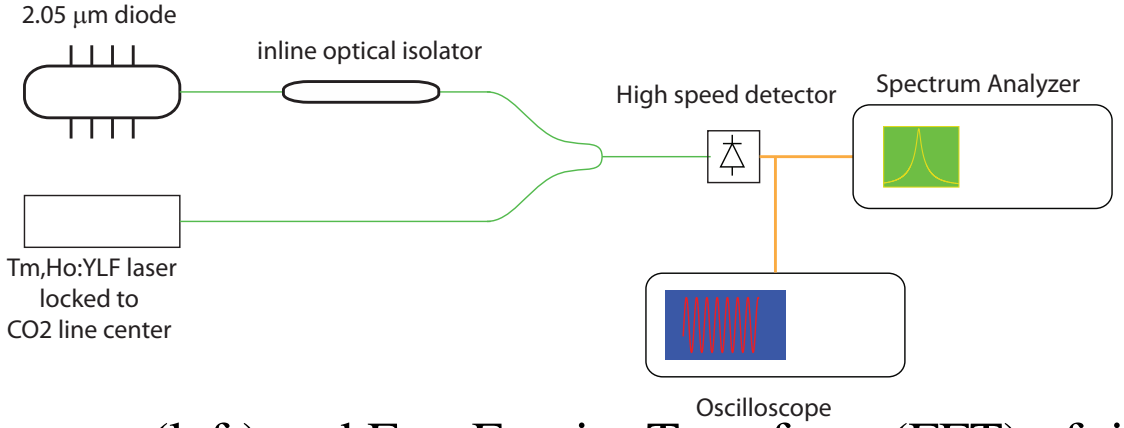


$$S_i(f) = (2\pi\tau_0\Delta i)^2 sinc(\tau_0 f)^2 S_v(f)$$
$$S_v(f) = \frac{\delta\nu}{\pi}$$

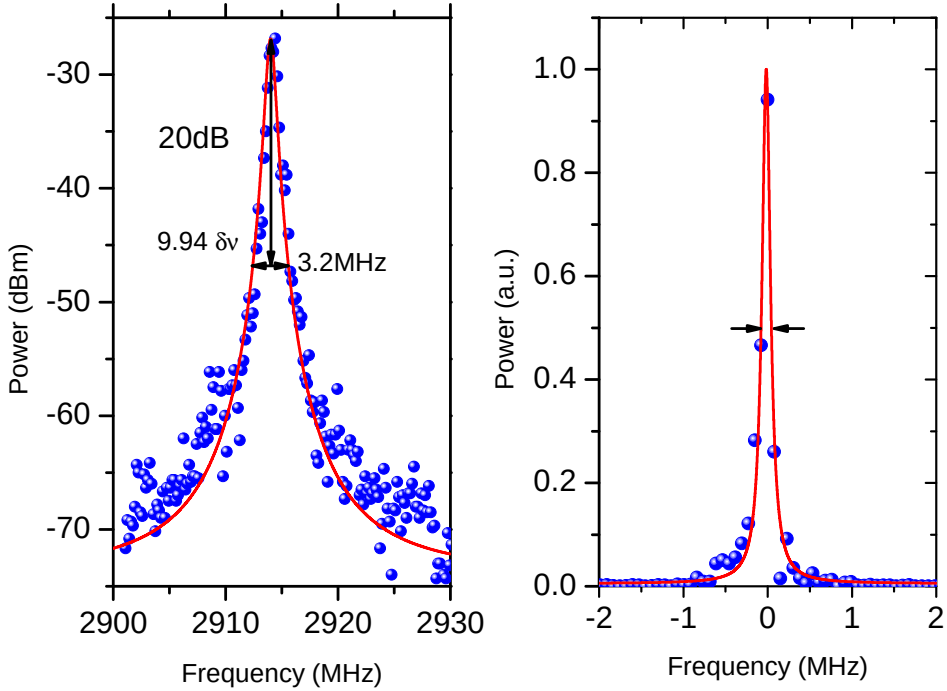
Linewidth < 30 KHz was measured for these lasers. The spectral purity is due to the small linewidth enhancement factor of this material system, long optical cavity and close to unity κL.

Laser Linewidth Measurement: Heterodyne setup

Beating a experiment setup

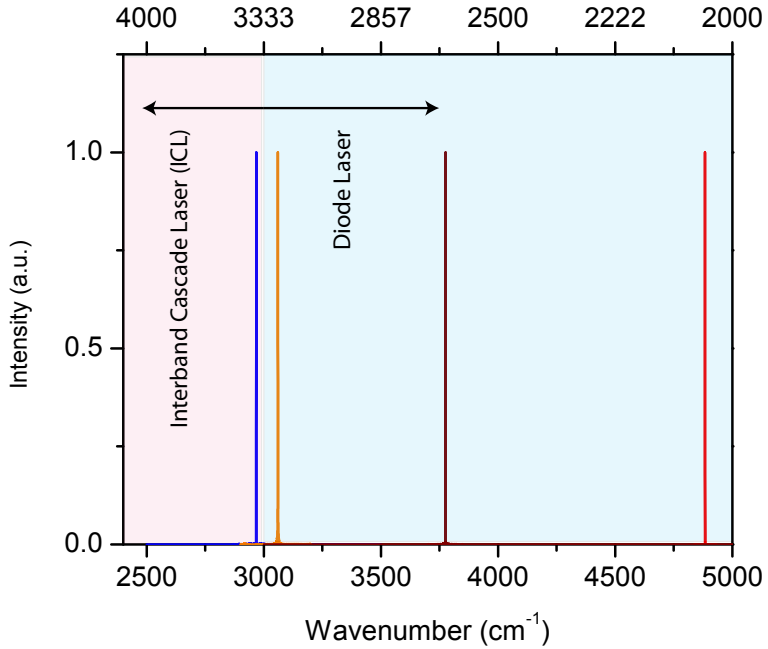


Beating spectrum (left) and Fast Fourier Transform (FFT) of time traces



JPL Semiconductor Laser Capabilities

Figure: JPL semiconductor laser inventory



- The GaSb based diode lasers cover a wide spectral range (2-3.5 μm)
- Beyond 3 μm, GaSb-based interband cascade lasers (ICLs) perform better
- Beyond 4 μm, demonstrated QCLs with record low power consumption (<1 W)

- We have successfully fabricated and delivered semiconductor lasers to a variety of different NASA missions
- End-to-end laser fabrication capability
- Space-qualification for semiconductor lasers
- Record high output power single mode semiconductor lasers in the mid-IR range
- Reliability measurement for semiconductor lasers

Conclusion

- ✓ High power fiber-pigtailed semiconductor lasers at 2.05 μm range have been realized
- ✓ The lasers show excellent side-mode suppression and spectral purity
- ✓ The lasers have less than 100 KHz natural linewidth
- ✓ The butterfly package modules with fiber-coupled output power facilitates implementation of fiber-based optical transmitters for airborne and space applications
- ✓ The polarization maintaining (PM) output fiber removes uncertainties associated with polarization drifts and improve measurement sensitivity

Acknowlegements

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